Silicon NPN Power Transistors 2SC1046

DESCRIPTION

·With TO-3 package

·High breakdown voltage

APPLICATIONS

·For CRT horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1000	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
P_C	Collector power dissipation	T_C=25?	25	W
T_j	Junction temperature		125	?
T_{stg}	Storage temperature		-40~125	?

CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=5mA; I_B=0	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA; I_E=0	1000			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=1mA; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2 A;I_B=0.4A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=800V;I_E=0			10	µA
I_{EBO}	Emitter cut-off current	V_{EB}=5V;I_C=0			10	µA
h_{FE}	DC current gain	I_C=2 A ; V_{CE}=5V	4		20	

PACKAGE OUTLINE

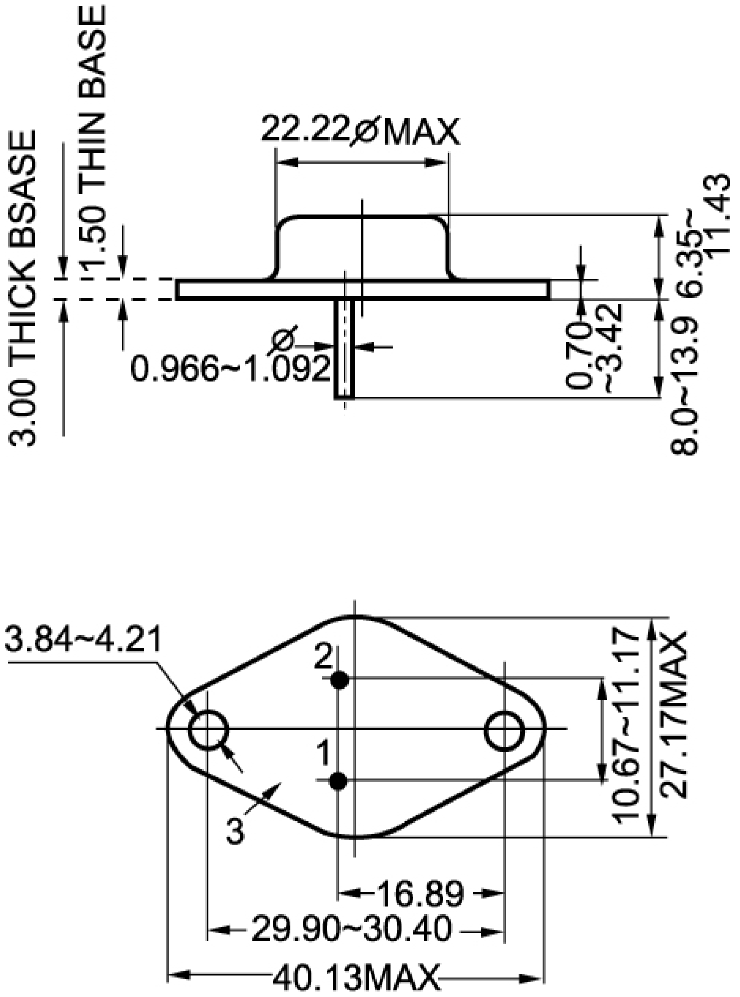

Fig.2 Outline dimensions